

Rad-Hard 16 Channel CMOS Analog Multiplexer with High-Z Analog Input Protection

The HS-1840ARH is a radiation hardened, monolithic 16 channel multiplexer constructed with the Intersil Rad-Hard Silicon Gate, bonded wafer, Dielectric Isolation process. It is designed to provide a high input impedance to the analog source if device power fails (open), or the analog signal voltage inadvertently exceeds the supply by up to $\pm 35V$, regardless of whether the device is powered on or off. Excellent for use in redundant applications, since the secondary device can be operated in a standby unpowered mode affording no additional power drain. More significantly, a very high impedance exists between the active and inactive devices preventing any interaction. One of sixteen channel selection is controlled by a 4-bit binary address plus an Enable-Inhibit input which conveniently controls the ON/OFF operation of several multiplexers in a system. All inputs have electrostatic discharge protection. The HSH1840ARH is processed and screened in full compliance with MIL-PRF-38535 and QML standards. The device is available in a 28 Ld SBDIP and a 28 Ld Ceramic Flatpack.

Specifications for Rad Hard QML devices are controlled by the Defense Supply Center in Columbus (DSCC). The SMD numbers listed here must be used when ordering.

Detailed Electrical Specifications for these devices are contained in SMD 5962-95630. A "hot-link" is provided on our homepage for downloading.

<http://www.intersil.com/spacedefense/space.htm>

Ordering Information

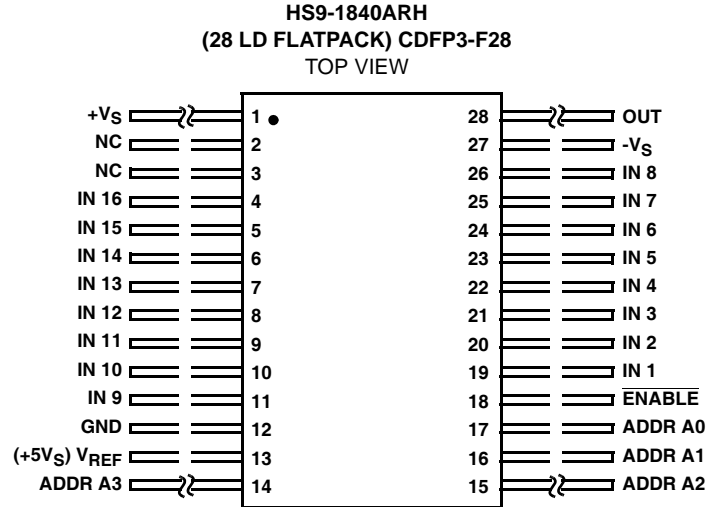
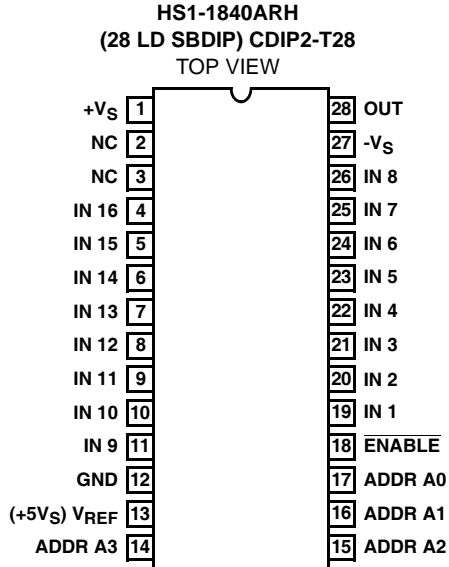
ORDERING NUMBER	INTERNAL MKT. NUMBER	TEMPERATURE RANGE (°C)	PART MARKING NO.	PACKAGE
5962F9563002QXC	HS1-1840ARH-8	-55 to 125	Q 5962F95 63002QXC	28 Ld SBDIP
5962F9563002QYC	HS9-1840ARH-8	-55 to 125	Q 5962F95 63002QYC	28 Ld Flatpack
5962F9563002VXC	HS1-1840ARH-Q	-55 to 125	Q 5962F95 63002VXC	28 Ld SBDIP
5962F9563002VYC	HS9-1840ARH-Q	-55 to 125	Q 5962F95 63002VYC	28 Ld Flatpack
HS1-1840ARH/PROTO	HS1-1840ARH/PROTO	-55 to 125	HS1- 1840ARH /PROTO	28 Ld SBDIP
HS9-1840ARH/PROTO	HS9-1840ARH/PROTO	-55 to 125	HS9- 1840ARH /PROTO	28 Ld Flatpack
HS1-1840ARH-T	HS1-1840ARH-T	-55 to 125	Q 5962R95 63002TXC	28 Ld SBDIP

Features

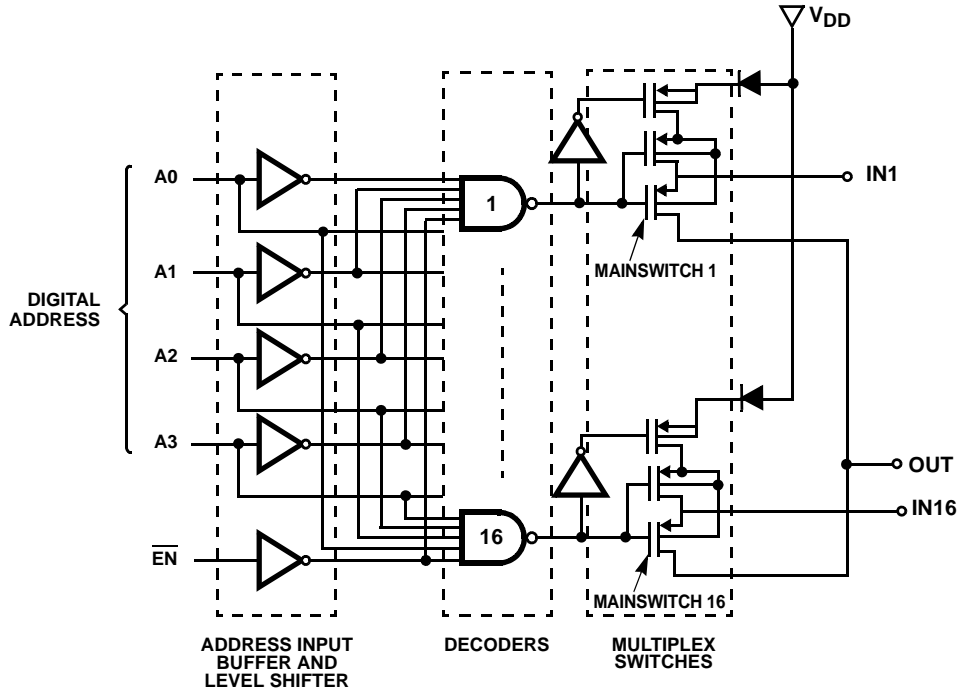
- Electrically Screened to SMD # 5962-95630
- QML Qualified per MIL-PRF-38535 Requirements
- Pin-to-Pin for Intersil's HS-1840RH and HS-1840/883S
- Improved Radiation Performance
 - Gamma Dose (γ) 3×10^5 RAD(Si)
- Improved $r_{DS(ON)}$ Linearity
- Improved Access Time 1.5 μ s (Max) Over Temp and Post Rad
- High Analog Input Impedance 500M Ω During Power Loss (Open)
- $\pm 35V$ Input Overvoltage Protection (Power On or Off)
- Dielectrically Isolated Device Islands
- Excellent in Hi-Rel Redundant Systems
- Break-Before-Make Switching
- No Latch-Up

HS-1840ARH

Pinouts



Functional Diagram



NOTE: MAINSWITCH INXX: SWITCH ON, BODY TIED TO SOURCE
SWITCH OFF, BODY TIED TO VCC-0.7V

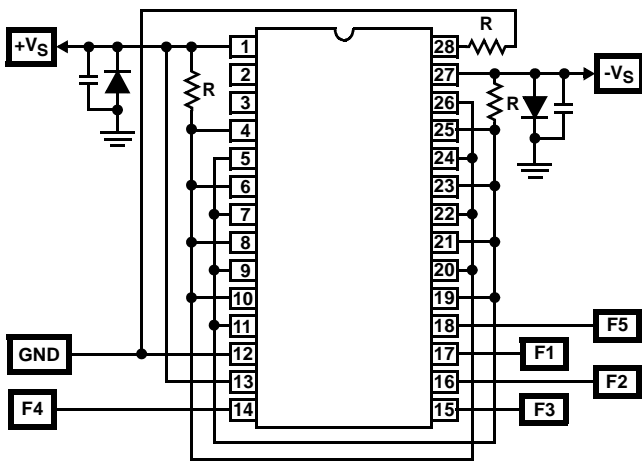
TABLE 1. TRUTH TABLE

A3	A2	A1	A0	$\overline{\text{EN}}$	"ON" CHANNEL
X	X	X	X	H	None
L	L	L	L	L	1
L	L	L	H	L	2
L	L	H	L	L	3
L	L	H	H	L	4

TABLE 1. TRUTH TABLE (Continued)

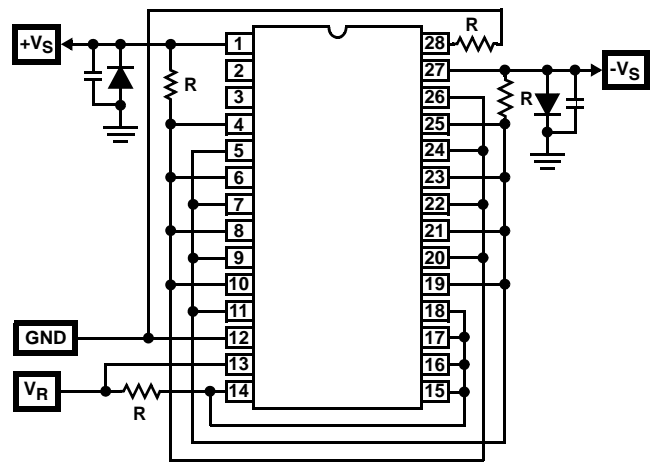
A3	A2	A1	A0	$\overline{\text{EN}}$	"ON" CHANNEL
L	H	L	L	L	5
L	H	L	H	L	6
L	H	H	L	L	7
L	H	H	H	L	8
H	L	L	L	L	9
H	L	L	H	L	10
H	L	H	L	L	11
H	L	H	H	L	12
H	H	L	L	L	13
H	H	L	H	L	14
H	H	H	L	L	15
H	H	H	H	L	16

Burn-In/Life Test Circuits



NOTE:
 $V_{S+} = +15.5V \pm 0.5V$, $V_{S-} = -15.5V \pm 0.5V$.
 $R = 1k\Omega \pm 5\%$.
 $C_1 = C_2 = 0.01\mu F \pm 10\%$, 1 EACH PER SOCKET, MINIMUM.
 $D_1 = D_2 = 1N4002$, 1 EACH PER BOARD, MINIMUM.
 INPUT SIGNALS:
 SQUARE WAVE, 50% DUTY CYCLE, 0V TO 15V PEAK $\pm 10\%$.
 $F_1 = 100kHz$; $F_2 = F_1/2$; $F_3 = F_1/4$; $F_4 = F_1/8$; $F_5 = F_1/16$.

FIGURE 1. DYNAMIC BURN-IN AND LIFE TEST CIRCUIT



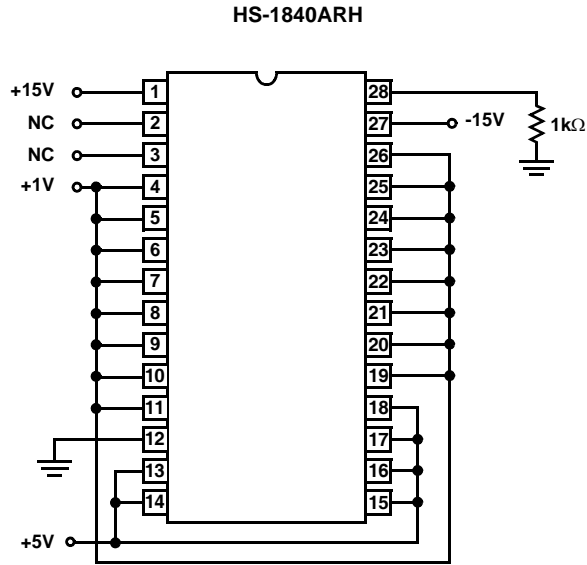
NOTE:
 $R = 1k\Omega \pm 5\%$, 1/4W.
 $C_1 = C_2 = 0.01\mu F$ MINIMUM, 1 EACH PER SOCKET, MINIMUM.
 $V_{S+} = 15.5V \pm 0.5V$, $V_{S-} = -15.5V \pm 0.5V$, $V_R = 15.5 \pm 0.5V$

FIGURE 2. .STATIC BURN-IN TEST CIRCUIT

NOTES:

1. The above test circuits are utilized for all package types.
2. The Dynamic Test Circuit is utilized for all life testing.

Irradiation Circuit



NOTE:

- 3. All irradiation testing is performed in the 28 lead CERDIP package.

Die Characteristics

DIE DIMENSIONS:

(2820 μ m x 4080 μ m x 483 μ m \pm 25.4 μ m)
 111 mils x 161 mils x 19 mils \pm 1 mil

INTERFACE MATERIALS:

Glassivation:

Type: PSG (Phosphorus Silicon Glass)
 Thickness: 8.0k Å \pm 1k Å

Top Metallization:

Type: AlSiCu
 Thickness: 16.0k Å \pm 2k Å

Backside Finish:

Silicon

ASSEMBLY RELATED INFORMATION:

Substrate Potential:

Unbiased (DI)

ADDITIONAL INFORMATION:

Worst Case Current Density:

Modified SEM

Transistor Count:

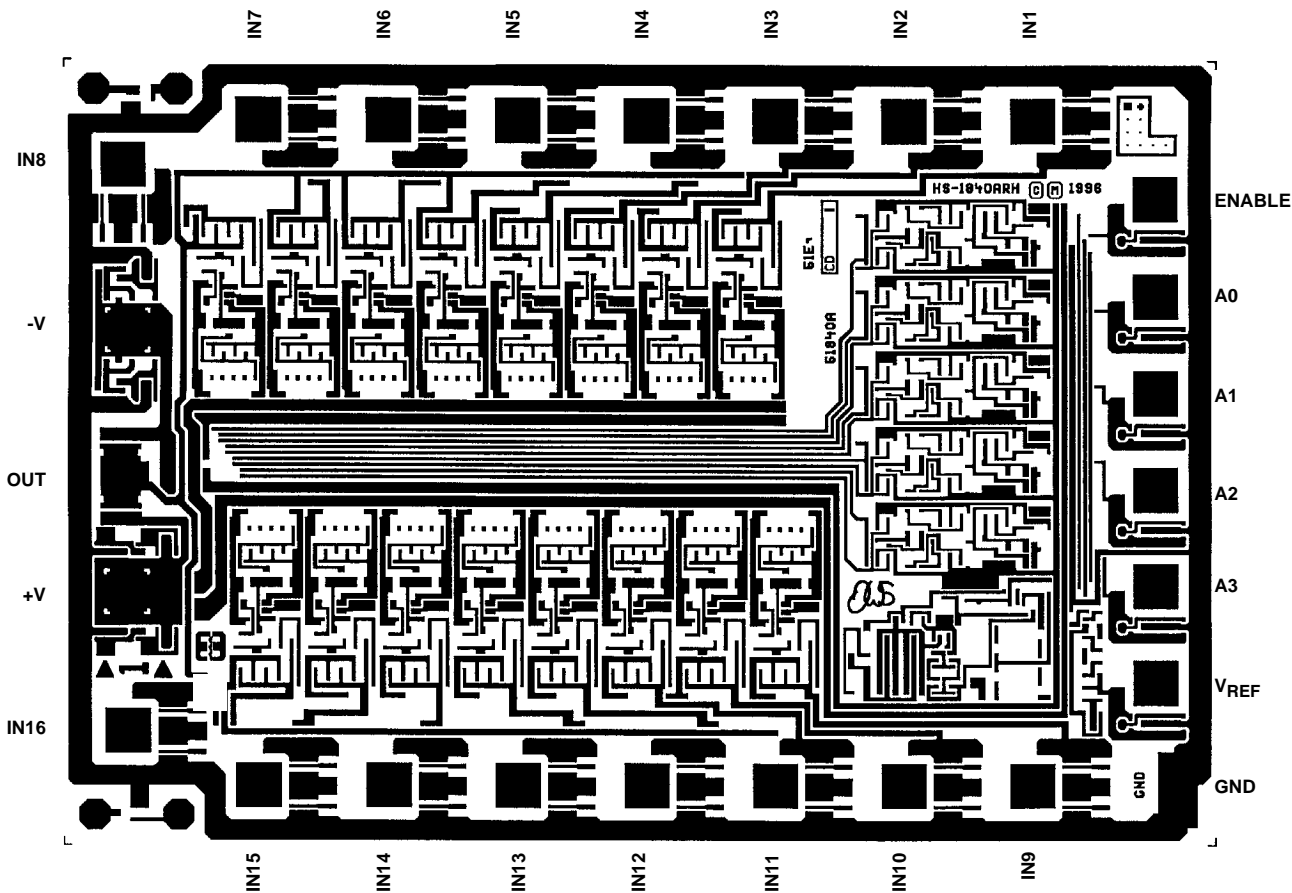
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Process:

Radiation Hardened Silicon Gate,
 Bonded Wafer, Dielectric Isolation

Metallization Mask Layout

HS-1840ARH

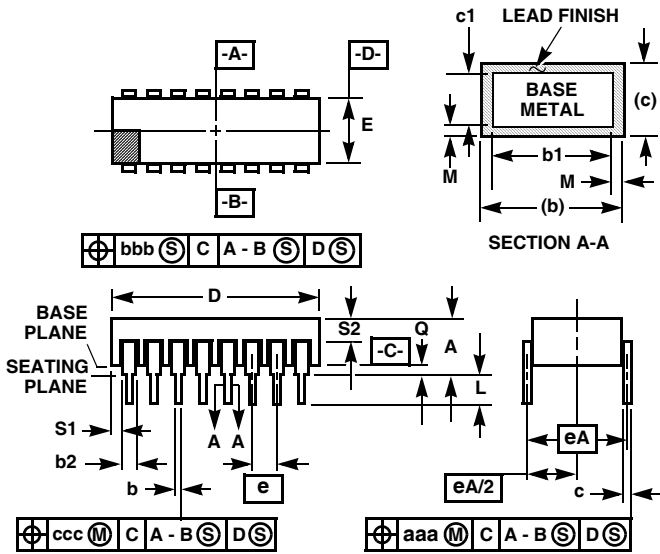


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Ceramic Dual-In-Line Metal Seal Packages (SBDIP)



NOTES:

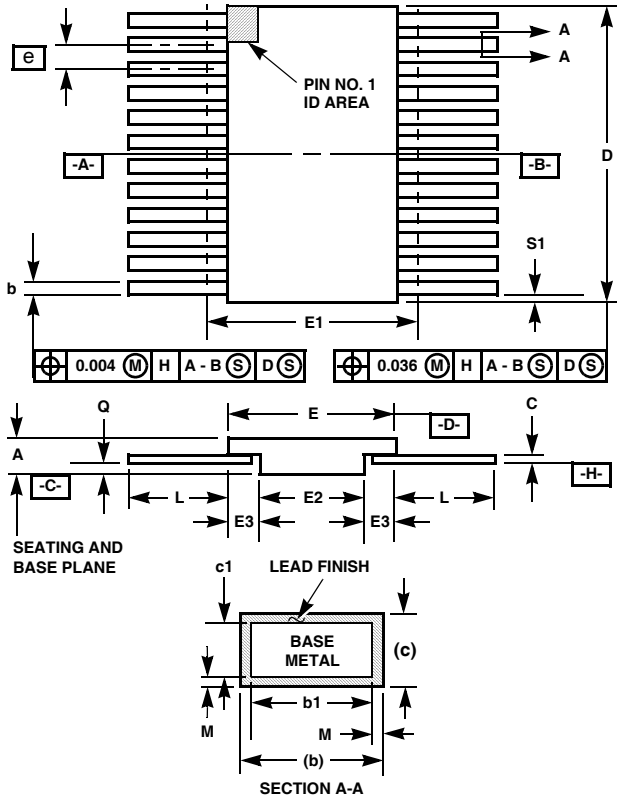
4. Index area: A notch or a pin one identification mark shall be located adjacent to pin one and shall be located within the shaded area shown. The manufacturer's identification shall not be used as a pin one identification mark.
5. The maximum limits of lead dimensions b and c or M shall be measured at the centroid of the finished lead surfaces, when solder dip or tin plate lead finish is applied.
6. Dimensions b1 and c1 apply to lead base metal only. Dimension M applies to lead plating and finish thickness.
7. Corner leads (1, N, N/2, and N/2+1) may be configured with a partial lead paddle. For this configuration dimension b3 replaces dimension b2.
8. Dimension Q shall be measured from the seating plane to the base plane.
9. Measure dimension S1 at all four corners.
10. Measure dimension S2 from the top of the ceramic body to the nearest metallization or lead.
11. N is the maximum number of terminal positions.
12. Braze fillets shall be concave.
13. Dimensioning and tolerancing per ANSI Y14.5M - 1982.
14. Controlling dimension: INCH.

D28.6 MIL-STD-1835 CDIP2-T28 (D-10, CONFIGURATION C)
28 LEAD CERAMIC DUAL-IN-LINE METAL SEAL PACKAGE

SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN	MAX	MIN	MAX	
A	-	0.232	-	5.92	-
b	0.014	0.026	0.36	0.66	2
b1	0.014	0.023	0.36	0.58	3
b2	0.045	0.065	1.14	1.65	-
b3	0.023	0.045	0.58	1.14	4
c	0.008	0.018	0.20	0.46	2
c1	0.008	0.015	0.20	0.38	3
D	-	1.490	-	37.85	-
E	0.500	0.610	12.70	15.49	-
e	0.100 BSC		2.54 BSC		-
eA	0.600 BSC		15.24 BSC		-
eA/2	0.300 BSC		7.62 BSC		-
L	0.125	0.200	3.18	5.08	-
Q	0.015	0.060	0.38	1.52	5
S1	0.005	-	0.13	-	6
S2	0.005	-	0.13	-	7
α	90°	105°	90°	105°	-
aaa	-	0.015	-	0.38	-
bbb	-	0.030	-	0.76	-
ccc	-	0.010	-	0.25	-
M	-	0.0015	-	0.038	2
N	28		28		8

Rev. 0 5/18/94

Ceramic Metal Seal Flatpack Packages (Flatpack)



**K28.A MIL-STD-1835 CDFP3-F28 (F-11A, CONFIGURATION B)
28 LEAD CERAMIC METAL SEAL FLATPACK PACKAGE**

SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN	MAX	MIN	MAX	
A	0.045	0.115	1.14	2.92	-
b	0.015	0.022	0.38	0.56	-
b1	0.015	0.019	0.38	0.48	-
c	0.004	0.009	0.10	0.23	-
c1	0.004	0.006	0.10	0.15	-
D	-	0.740	-	18.80	3
E	0.460	0.520	11.68	13.21	-
E1	-	0.550	-	13.97	3
E2	0.180	-	4.57	-	-
E3	0.030	-	0.76	-	7
e	0.050 BSC		1.27 BSC		-
k	0.008	0.015	0.20	0.38	2
L	0.250	0.370	6.35	9.40	-
Q	0.026	0.045	0.66	1.14	8
S1	0.00	-	0.00	-	6
M	-	0.0015	-	0.04	-
N	28		28		-

Rev. 0 5/18/94

NOTES:

1. Index area: A notch or a pin one identification mark shall be located adjacent to pin one and shall be located within the shaded area shown. The manufacturer's identification shall not be used as a pin one identification mark. Alternately, a tab (dimension k) may be used to identify pin one.
2. If a pin one identification mark is used in addition to a tab, the limits of dimension k do not apply.
3. This dimension allows for off-center lid, meniscus, and glass overrun.
4. Dimensions b1 and c1 apply to lead base metal only. Dimension M applies to lead plating and finish thickness. The maximum limits of lead dimensions b and c or M shall be measured at the centroid of the finished lead surfaces, when solder dip or tin plate lead finish is applied.
5. N is the maximum number of terminal positions.
6. Measure dimension S1 at all four corners.
7. For bottom-brazed lead packages, no organic or polymeric materials shall be molded to the bottom of the package to cover the leads.
8. Dimension Q shall be measured at the point of exit (beyond the meniscus) of the lead from the body. Dimension Q minimum shall be reduced by 0.0015 inch (0.038mm) maximum when solder dip lead finish is applied.
9. Dimensioning and tolerancing per ANSI Y14.5M - 1982.
10. Controlling dimension: INCH.